



# TR STP9NK90Z;ST;TO220;tranzystor; N-MOSFET;8A;900V;160W;1.1R;RoHS



## Dane techniczne:

Nazwa: STP9NK90Z

Typ tranzystora: unipolarny

Kierunek przewodnictwa: N-MOSFET

Prąd kolektora: 8A

Napięcie kolektor-emiter: 900V

Moc: 160W

Montaż: przewlekany(THT)

Obudowa: TO220

Producent: ST



# STB9NK90Z, STF9NK90Z STP9NK90Z, STW9NK90Z

N-channel 900 V, 1.1  $\Omega$ , 8 A, TO-220, TO-220FP, D<sup>2</sup>PAK, TO-247  
Zener-protected SuperMESH™ Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on) max.</sub>	I <sub>D</sub>	P <sub>w</sub>
STB9NK90Z	900V	<1.3 $\Omega$	8A	160 W
STW9NK90Z				160 W
STP9NK90Z				160 W
STF9NK90Z				40 W

- Extremely high dv/dt capability
- 100% avalanche tested
- Gate charge minimized

## Application

- Switching applications

## Description

The SuperMESH™ series is obtained through an optimization of STMicroelectronics' well-established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly lower, it also ensures very good dv/dt capability for the most demanding applications. This series complement STs' full range of high voltage power MOSFETs.

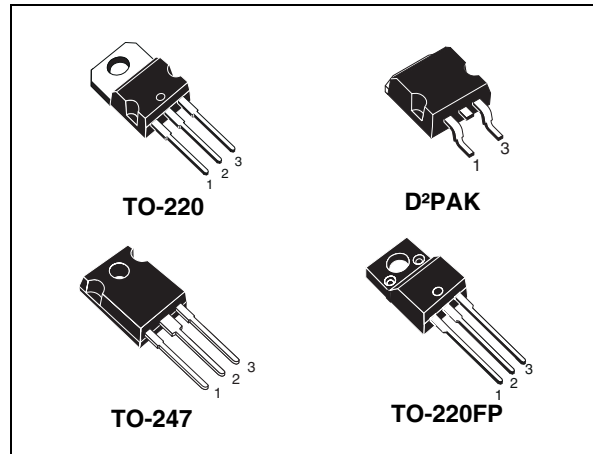


Figure 1. Internal schematic diagram

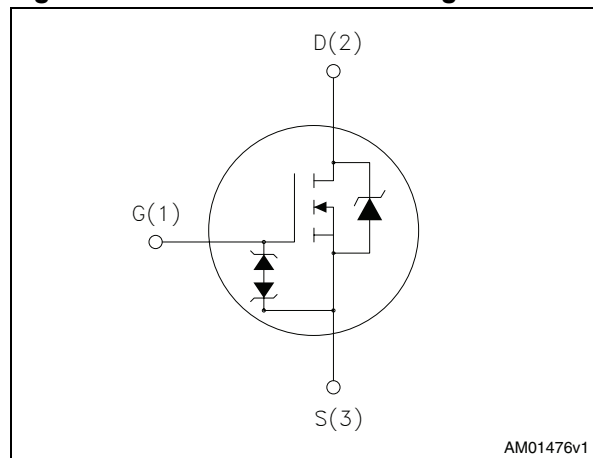


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB9NK90Z	B9NK90	D <sup>2</sup> PAK	Tape and reel
STF9NK90Z	F9NK90Z	TO-220FP	Tube
STP9NK90Z	P9NK90Z	TO-220	
STW9NK90Z	W9NK90Z	TO-247	

# Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>4</b>
2.1	Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits</b> .....	<b>9</b>
<b>4</b>	<b>Package mechanical data</b> .....	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b> .....	<b>15</b>
<b>6</b>	<b>Revision history</b> .....	<b>16</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value		Unit
		TO-220, D <sup>2</sup> PAK TO-247	TO-220FP	
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	900		V
V <sub>GS</sub>	Gate-source voltage	± 30		V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	8	8 <sup>(1)</sup>	A
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> =100 °C	5	5 <sup>(1)</sup>	A
I <sub>DM</sub> <sup>(2)</sup>	Drain current (pulsed)	32	32 <sup>(1)</sup>	A
P <sub>TOT</sub>	Total dissipation at T <sub>C</sub> = 25 °C	160	40	W
	Derating Factor	1.28	0.32	W/°C
Vesd(G-S)	G-S ESD (HBM C=100 pF, R=1.5 kΩ)	4		KV
dv/dt <sup>(3)</sup>	Peak diode recovery voltage slope	4.5		V/ns
V <sub>ISO</sub>	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1s;T <sub>C</sub> =25°C)	--	2500	V
T <sub>J</sub> T <sub>stg</sub>	Operating junction temperature Storage temperature	-55 to 150		°C

- Limited only by maximum temperature allowed
- Pulse width limited by safe operating area
- $I_{SD} \leq 10 \text{ A}$ ,  $di/dt \leq 200 \text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_j \leq T_{Jmax}$ .

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220 D <sup>2</sup> PAK	TO-220FP	TO-247	
R <sub>thj-case</sub>	Thermal resistance junction-case max	0.78	3.1	0.78	°C/W
R <sub>thj-a</sub>	Thermal resistance junction-ambient max	62.5		50	°C/W
T <sub>l</sub>	Maximum lead temperature for soldering purpose	300			°C

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
I <sub>AR</sub>	Avalanche current, repetitive or not-repetitive (pulse width limited by T <sub>j</sub> max.)	8	A
E <sub>AS</sub>	Single pulse avalanche energy (starting T <sub>J</sub> =25 °C, I <sub>D</sub> = I <sub>AR</sub> , V <sub>DD</sub> = 50 V) (see Figure 22)(see Figure 23)	300	mJ

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	900			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = \text{max rating}$ , $V_{DS} = \text{max rating @ } 125\text{ °C}$			1 50	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0$			$\pm 10$	$\mu\text{A}$
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 100\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$ , $I_D = 3.6\text{ A}$		1.1	1.3	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	2115	-	pF
$C_{oss}$	Output capacitance			190		
$C_{rss}$	Reverse transfer capacitance			40		
$C_{oss\text{ eq}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }720\text{ V}$	-	115	-	pF
$Q_g$	Total gate charge	$V_{DD} = 720\text{ V}$ , $I_D = 8\text{ A}$ $V_{GS} = 10\text{ V}$ <i>Figure 20</i>	-	72	-	nC
$Q_{gs}$	Gate-source charge			14		
$Q_{gd}$	Gate-drain charge			38		

1.  $C_{oss\text{ eq}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 450\text{ V}$ , $I_D = 4\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$	-	22	-	ns
$t_r$	Rise Time			13		ns
$t_{d(off)}$	Turn-off delay time	<i>Figure 19</i> <i>Figure 24</i>	-	55	-	ns
$t_f$	Fall time			28		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$I_{SD}$	Source-drain current		-		8	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)			32	A	
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 8\text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 8\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ , $V_{DD} = 50\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$ <i>Figure 21</i>	-	950		ns
$Q_{rr}$	Reverse recovery charge			10		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			21		A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration=300  $\mu\text{s}$ , duty cycle 1.5%

**Table 9. Gate-source Zener diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$ (open drain)	30	-		V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D<sup>2</sup>PAK

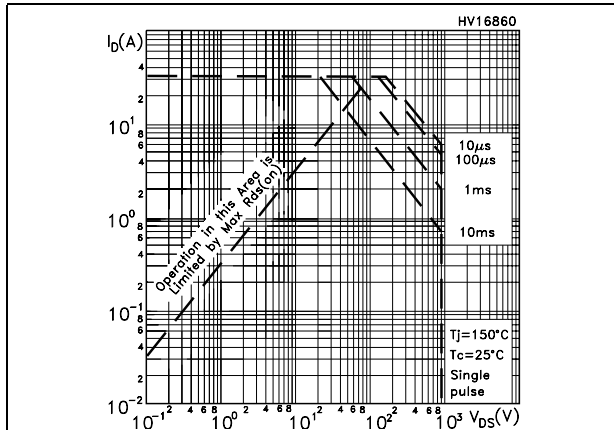


Figure 3. Thermal impedance for TO-220, D<sup>2</sup>PAK

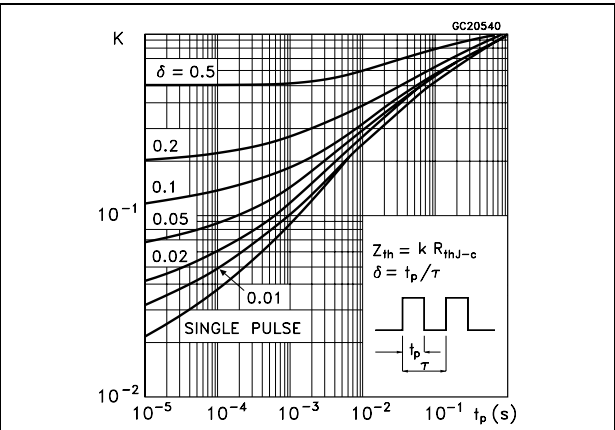


Figure 4. Safe operating area for TO-220FP

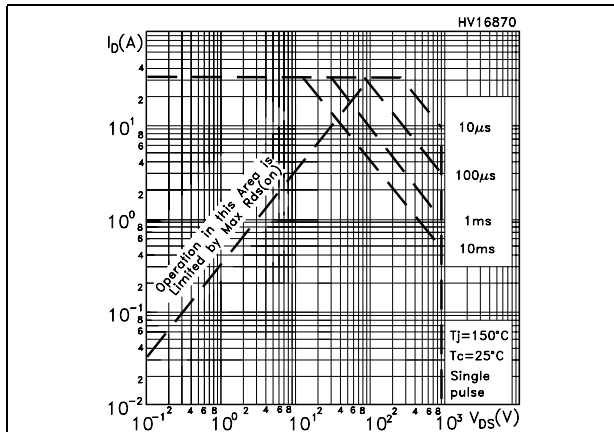


Figure 5. Thermal impedance for TO-220FP

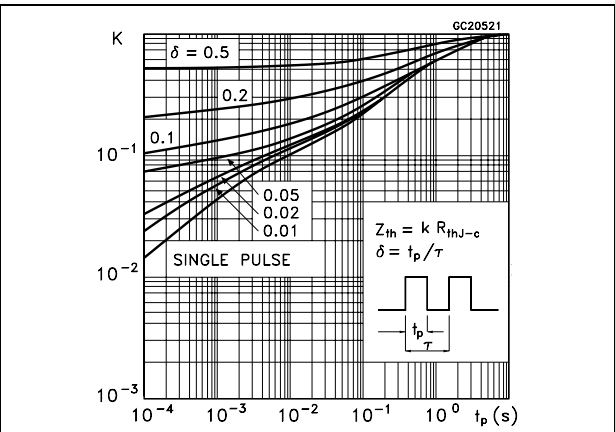


Figure 6. Safe operating area for TO-247

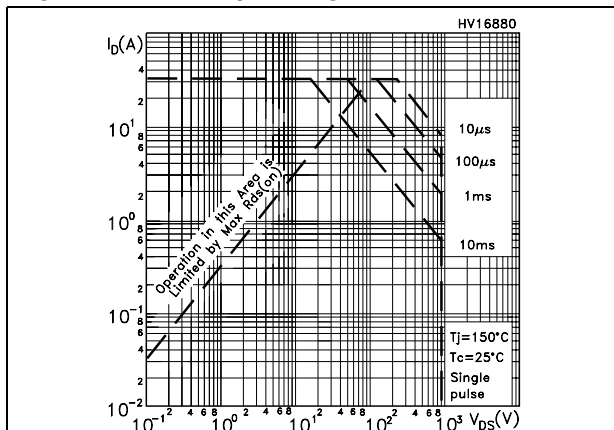


Figure 7. Thermal impedance for TO-247

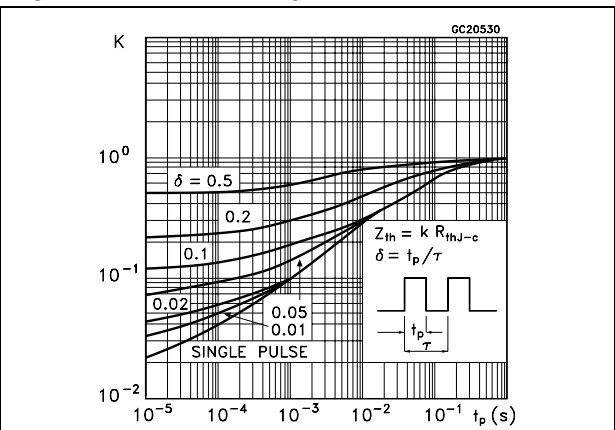


Figure 8. Output characteristics

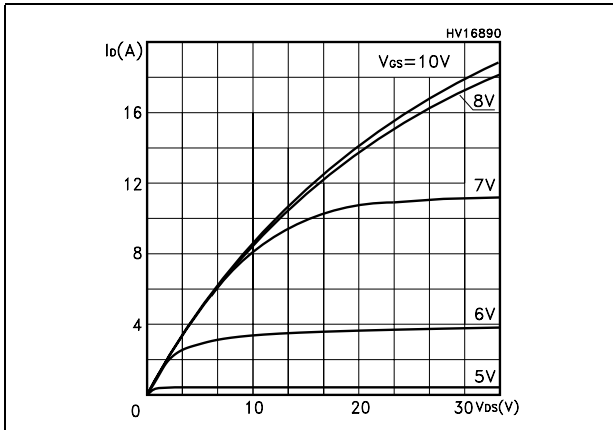


Figure 9. Transfer characteristics

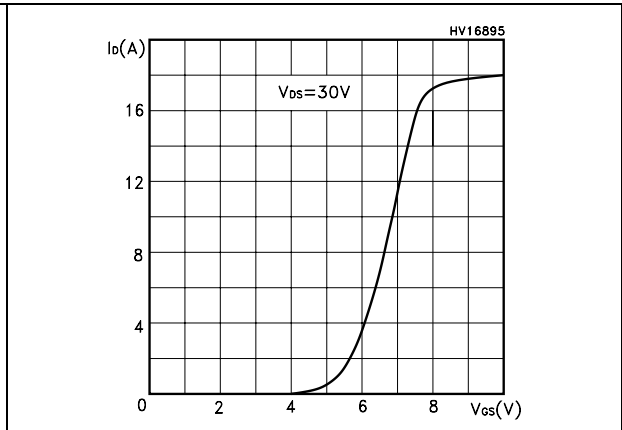


Figure 10. Transconductance

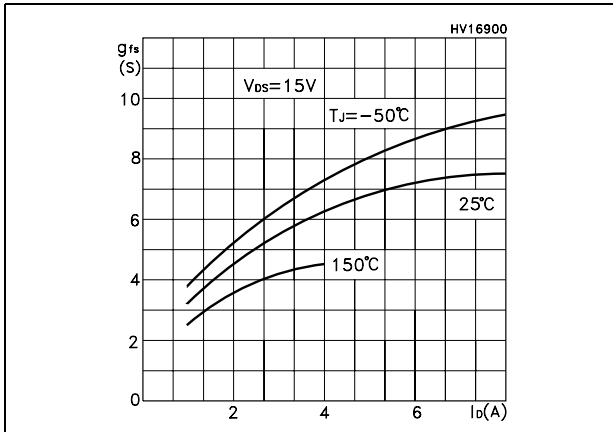


Figure 11. Static drain-source on resistance

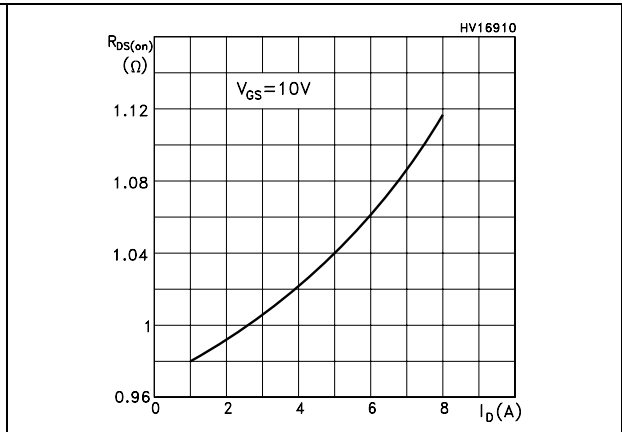


Figure 12. Gate charge vs gate-source voltage

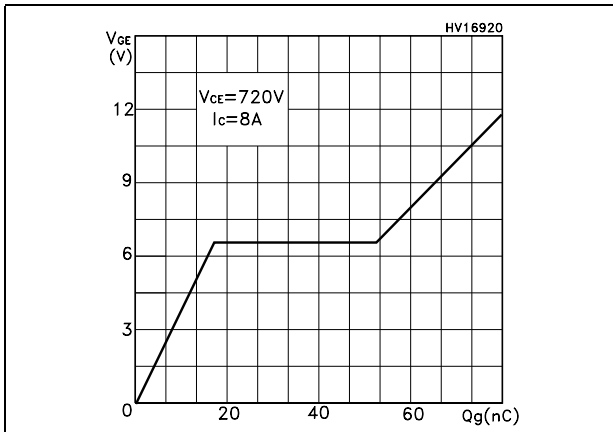


Figure 13. Capacitance variations

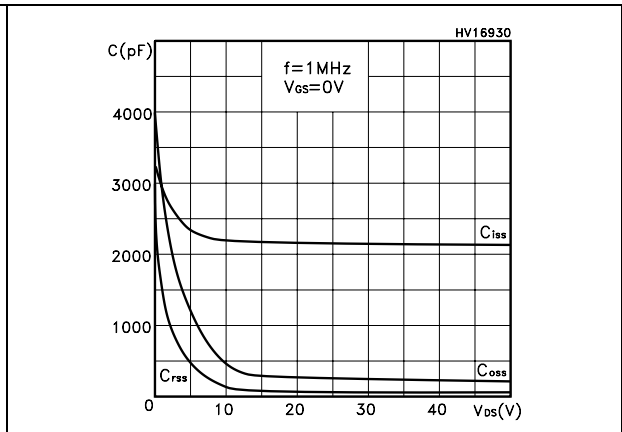




Figure 14. Normalized gate threshold voltage vs temperature

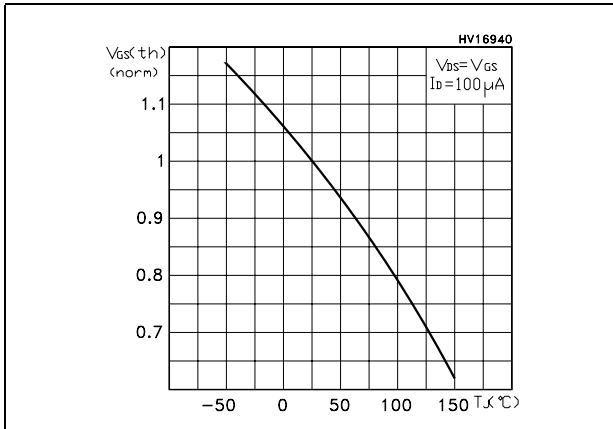


Figure 15. Normalized on resistance vs temperature

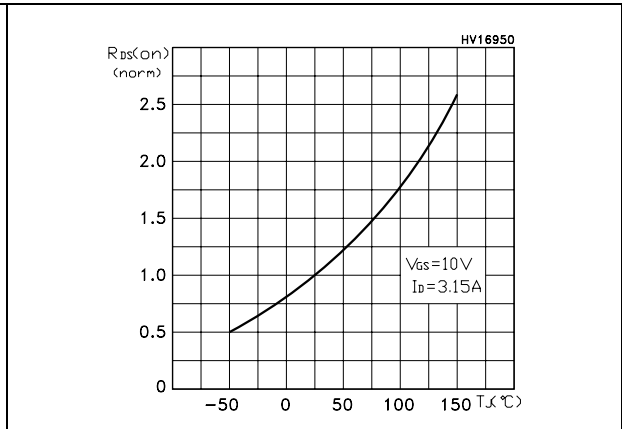


Figure 16. Source-drain diode forward characteristics

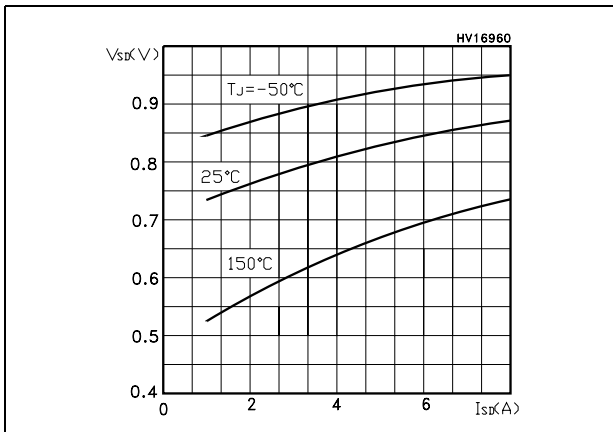


Figure 17. Normalized  $B_{V_{DSS}}$  vs temperature

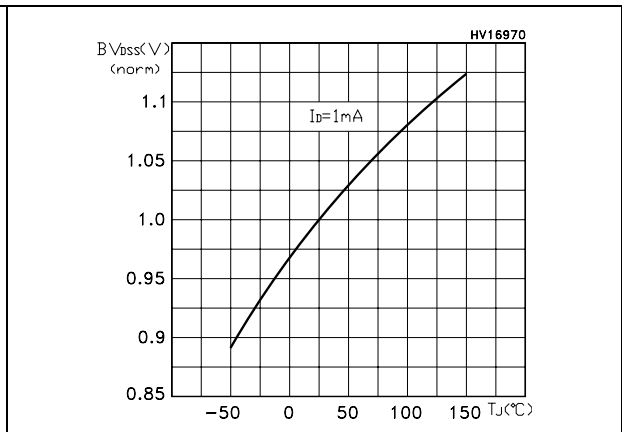
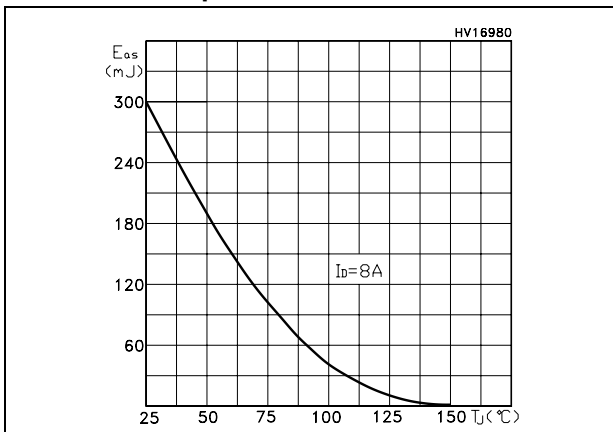
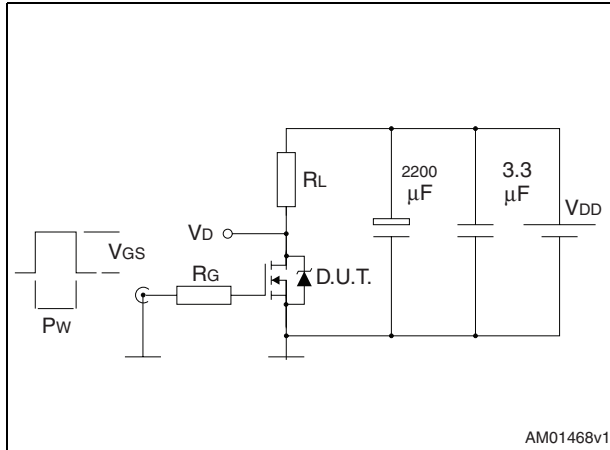


Figure 18. Maximum avalanche energy vs temperature

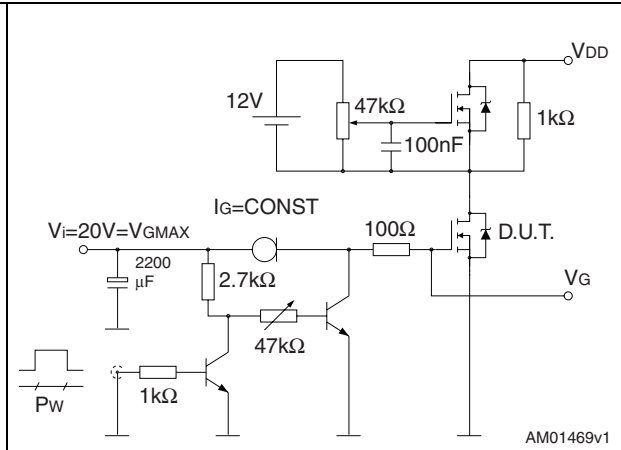


### 3 Test circuits

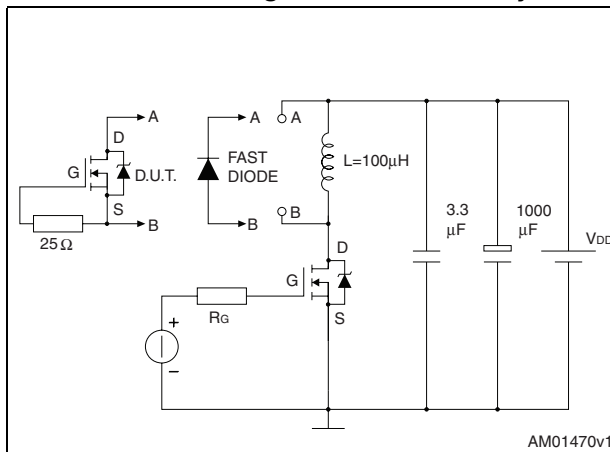
**Figure 19. Switching times test circuit for resistive load**



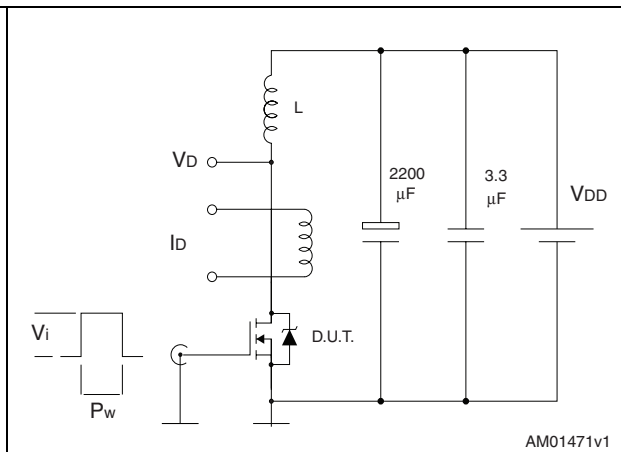
**Figure 20. Gate charge test circuit**



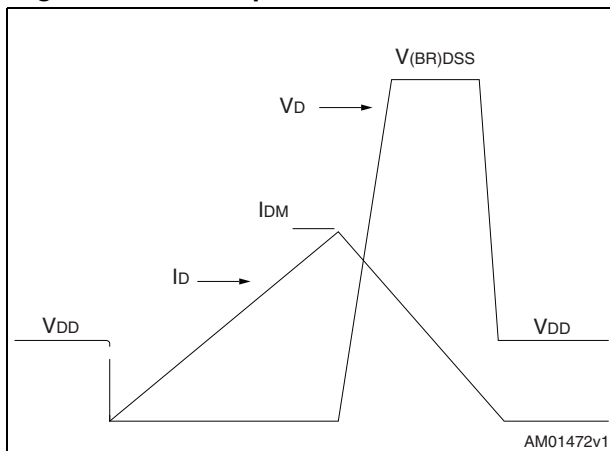
**Figure 21. Test circuit for inductive load switching and diode recovery times**



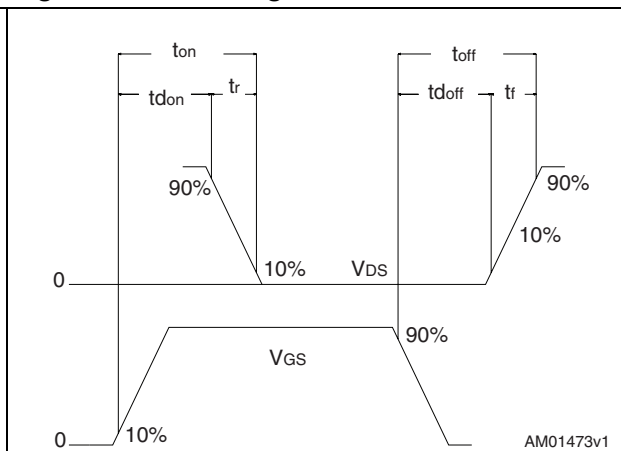
**Figure 22. Unclamped Inductive load test circuit**



**Figure 23. Unclamped inductive waveform**



**Figure 24. Switching time waveform**



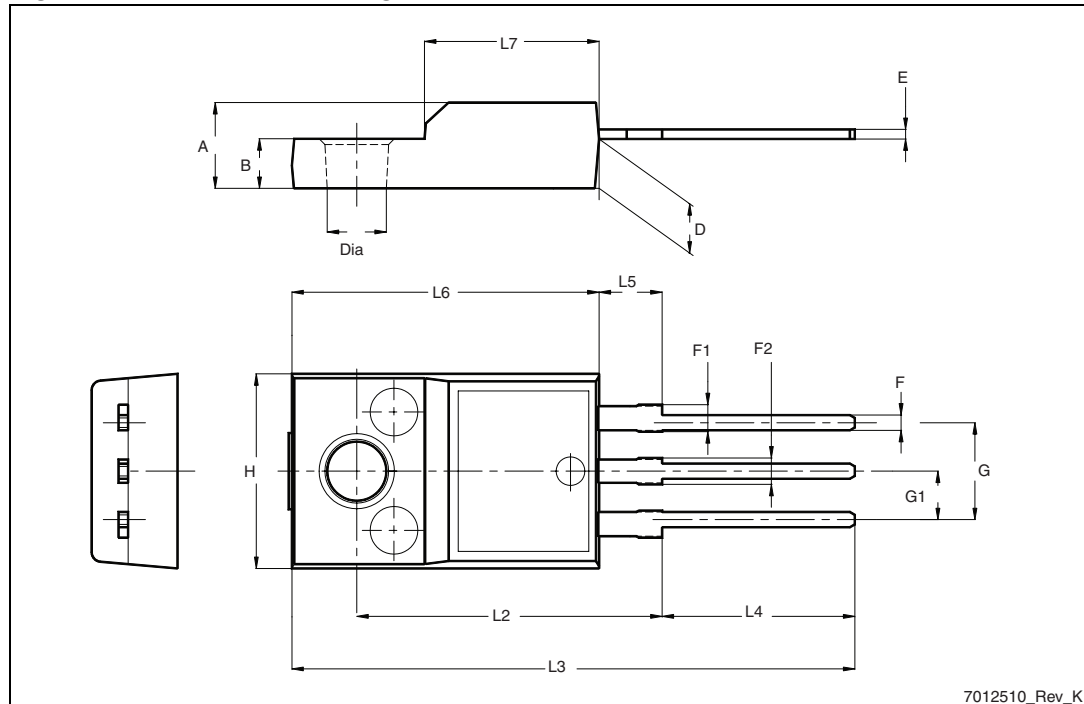
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

Table 10. TO-220FP mechanical data

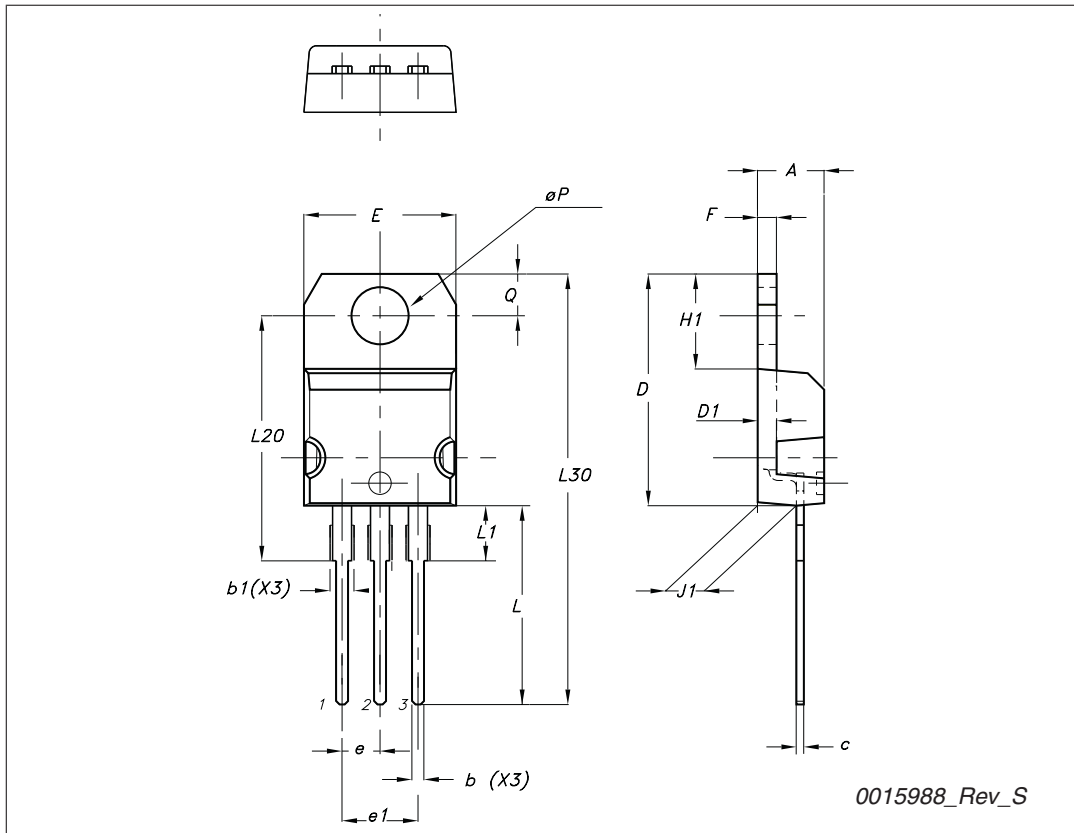
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 25. TO-220FP drawing



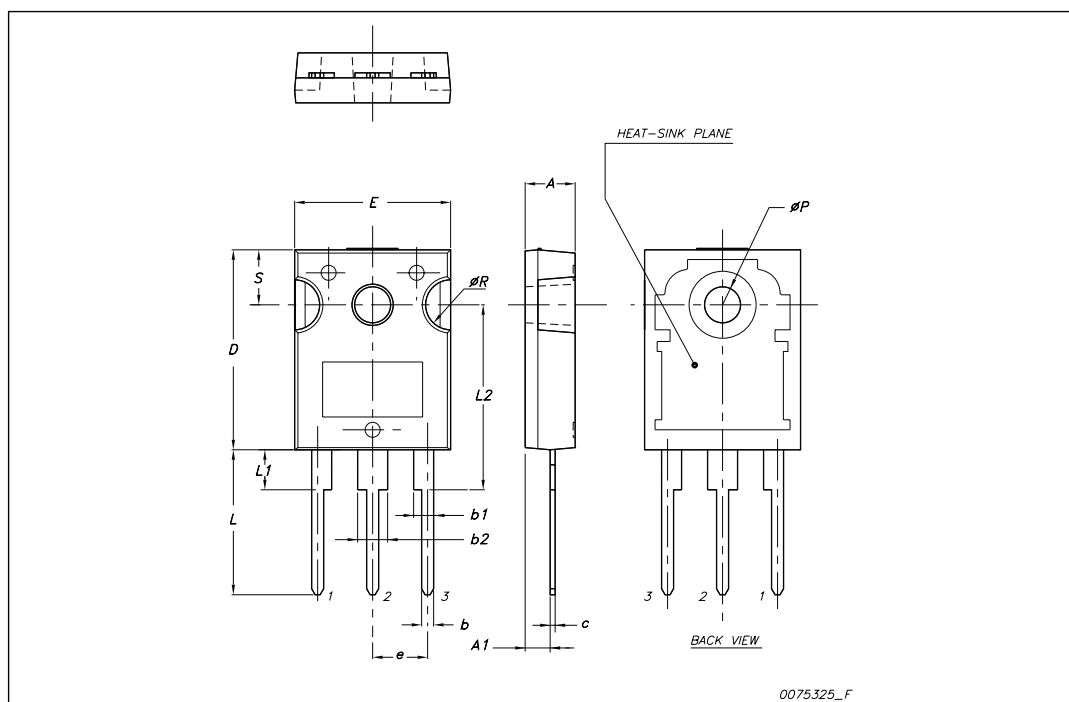
TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



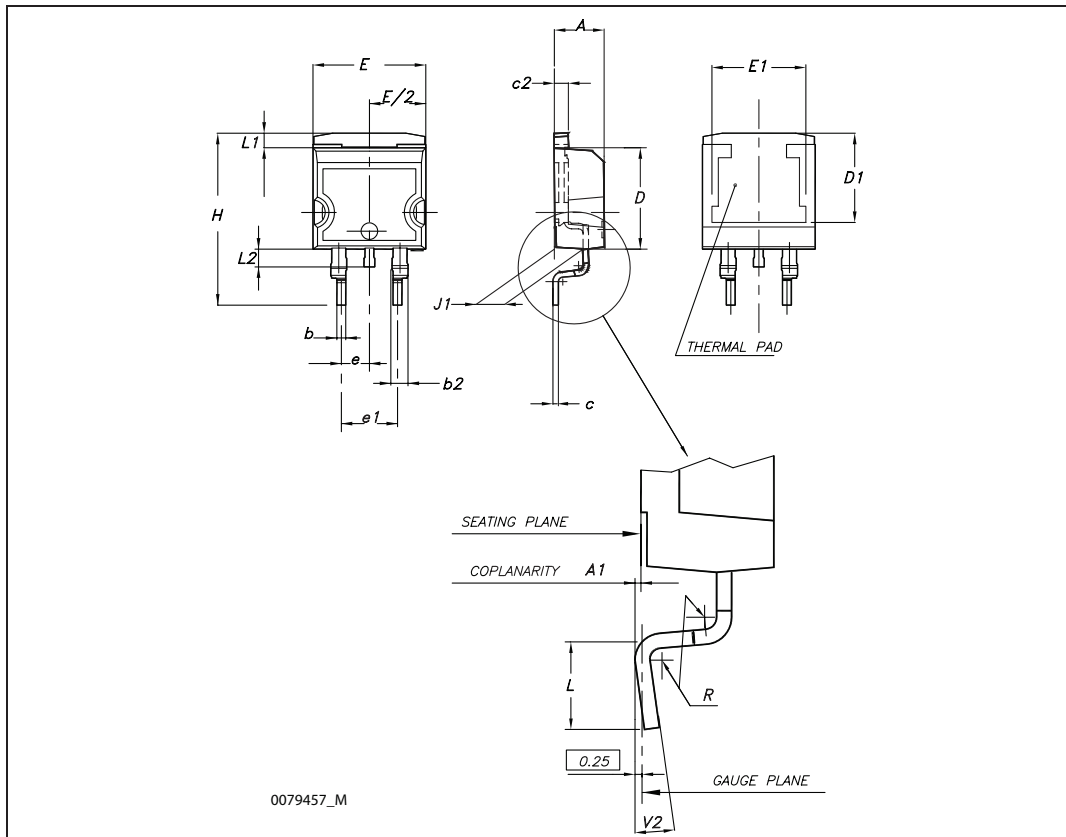
## TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



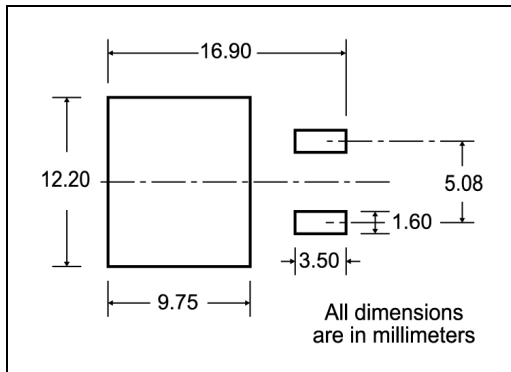
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



# 5 Packaging mechanical data

## D<sup>2</sup>PAK FOOTPRINT



## TAPE AND REEL SHIPMENT

**TAPE MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

**REEL MECHANICAL DATA**

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	24.4	26.4	0.960	1.039
N	100		3.937	
T		30.4		1.197

BASE QTY	BULK QTY
1000	1000

\* on sales type



## 6 Revision history

Table 11. Revision history

Date	Revision	Changes
08-Sep-2005	2	Complete version
27-Oct-2005	3	Inserted ecopack indication
20-Jul-2006	4	New template, no content change
20-Mar-2007	5	Typo mistake on cover page
13-Jul-2007	6	Corrected unit on <a href="#">Table 5.: On/off states</a>
19-May-2010	7	Corrected <a href="#">Figure 18: Maximum avalanche energy vs temperature</a>

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